

Philips

Diode BYD163

Datasheet

**Silicon Diode**

**BYD163**

600V/1A

**DATASHEET**

OEM – Philips

Source: Philips Databook 1999

**Ultra fast low-loss rectifier****BYD163****FEATURES**

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Available in ammo-pack.

**DESCRIPTION**

Cavity free cylindrical glass SOD81 package through Implotec™<sup>(1)</sup> technology. The SOD81 package is

hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

(1) Implotec is a trademark of Philips.

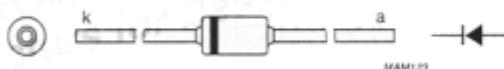


Fig.1 Simplified outline (SOD81) and symbol.

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RRM}$	repetitive peak reverse voltage			600	V
$V_R$	continuous reverse voltage			600	V
$I_{F(AV)}$	average forward current	$T_{tp} = 95^\circ\text{C}$ ; lead length = 10 mm; see Fig.5; averaged over any 20 ms period; see also Fig.6		1	A
$I_{FSM}$	non-repetitive peak forward current	$t = 10 \text{ ms}$ half sinewave; $V_R = V_{RRMmax}$		25	A
$T_{stg}$	storage temperature		-65	+175	$^\circ\text{C}$
$T_j$	junction temperature		-65	+175	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS**

$T_j = 25^\circ\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$V_F$	forward voltage	$I_F = 1 \text{ A}; T_j = 150^\circ\text{C}$ ; see Fig.2	1.05	V
		$I_F = 1 \text{ A}$ ; see Fig.2	1.25	V
$I_R$	reverse current	$V_R = V_{RRMmax}$ ; see Fig.3	5	$\mu\text{A}$
		$V_R = V_{RRMmax}; T_j = 150^\circ\text{C}$ ; see Fig.3	150	$\mu\text{A}$
$t_{rr}$	reverse recovery time	when switched from $I_F = 0.5 \text{ A}$ to $I_F = 1 \text{ A}$ ; measured at $I_R = 0.25 \text{ A}$	50	ns

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**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\-\text{tp}}$	thermal resistance from junction to tie-point	lead length = 10 mm	60	K/W
$R_{th\ j\-\text{a}}$	thermal resistance from junction to ambient	note 1	120	K/W

**Note**

1. Device mounted on epoxy-glass printed-circuit board, 1.5 mm thick; thickness of copper  $\geq 40 \mu\text{m}$ , see Fig.7.  
For more information please refer to the "General Part of associated Handbook".

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## GRAPHICAL DATA

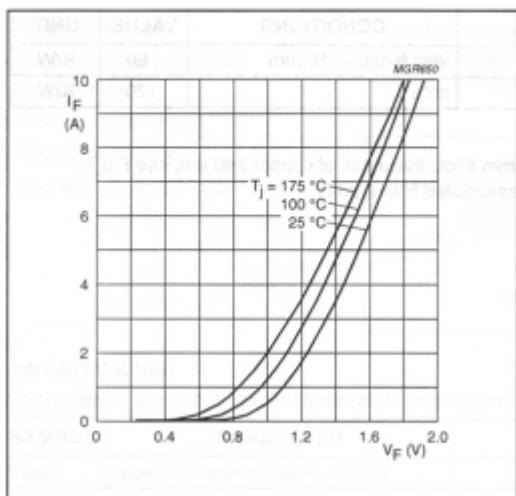


Fig.2 Forward current as a function of forward voltage; typical values.

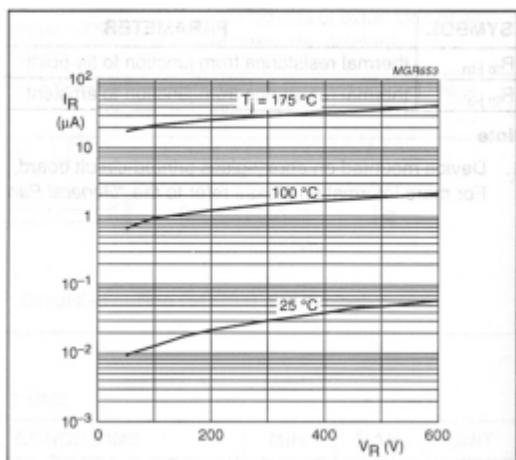


Fig.3 Reverse current as a function of reverse voltage; typical values.

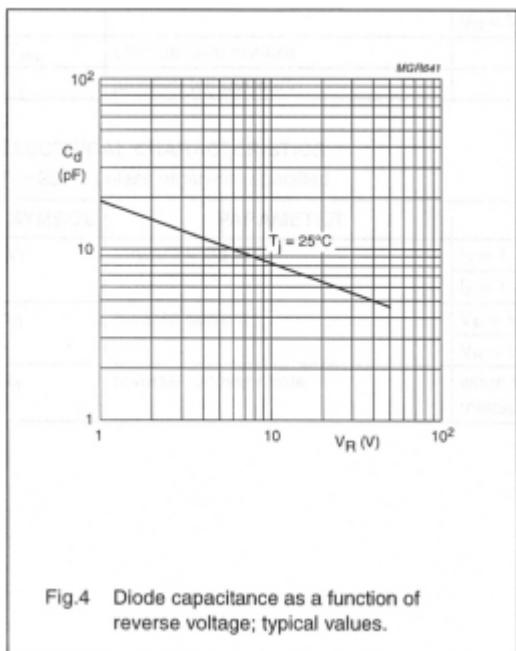


Fig.4 Diode capacitance as a function of reverse voltage; typical values.

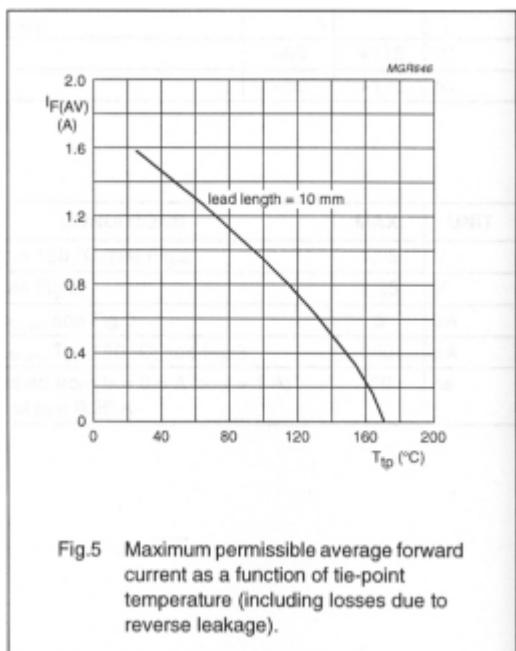


Fig.5 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).

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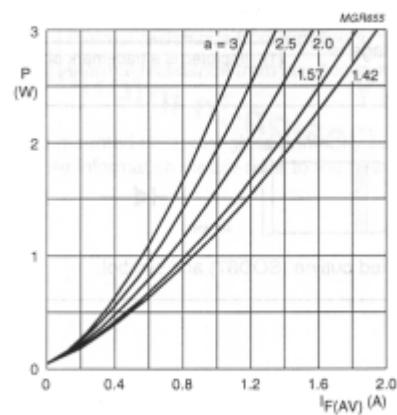
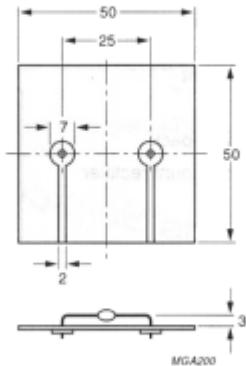


Fig.6 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.



Dimensions in mm.

Fig.7 Device mounted on a printed-circuit board.